

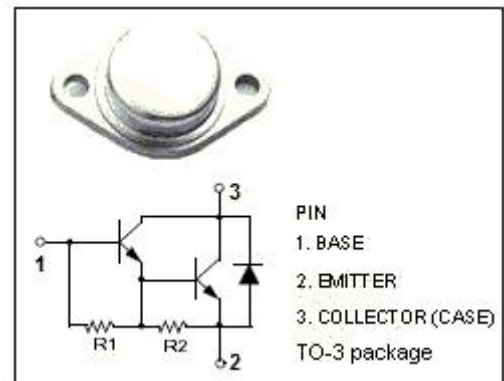
SPTECH Silicon NPN Darlington Power Transistor MJ11032

DESCRIPTION

- Collector-Emitter Breakdown Voltage
: $V_{(BR)CEO} = 120V(\text{Min.})$
- High DC Current Gain-
: $h_{FE} = 1000(\text{Min.})@I_C = 25A$
: $h_{FE} = 400(\text{Min.})@I_C = 50A$
- Complement to the PNP MJ11033

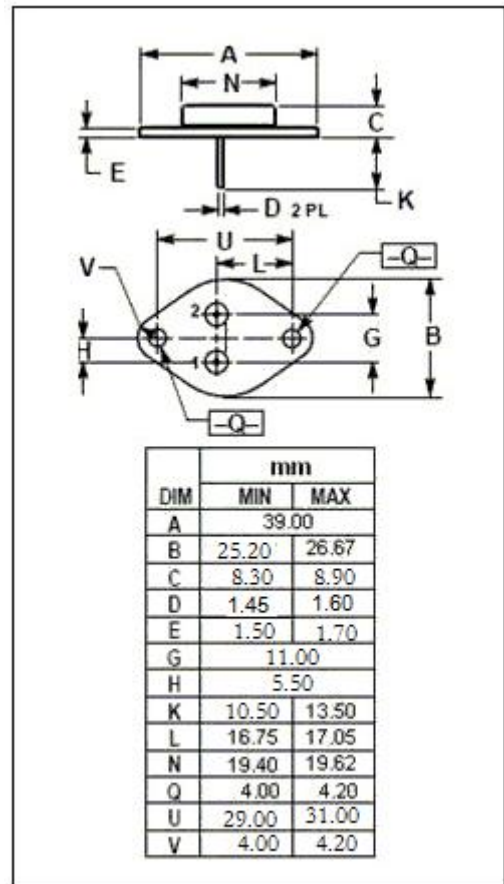
APPLICATIONS

- Designed for use as output devices in complementary general purpose amplifier applications.



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	50	A
I_{CM}	Collector Current-Peak	100	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	300	W
T_j	Junction Temperature	200	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~+200	$^\circ\text{C}$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.584	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _c = 50mA; I _B = 0	120			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _c = 25A; I _B = 250mA			2.5	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _c = 50A; I _B = 500mA			3.5	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _c = 25A; I _B = 250mA			3.0	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _c = 50A; I _B = 500mA			4.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} =120V; I _E =0 V _{CB} =120V; I _E =0; T _C =150°C			2.0 5.0	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 120V; I _B = 0			2.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			5.0	mA
h _{FE-1}	DC Current Gain	I _c = 25A, V _{CE} = 5V	1000		18000	
h _{FE-2}	DC Current Gain	I _c = 50A, V _{CE} = 5V	400			